

Ahmad Shuhaimi

List of Publications by Year in descending order

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100
papers

1,167
citations

471509

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434195

31
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102
all docs

102
docs citations

102
times ranked

1422
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Effects of graphene oxide concentration on optical properties of ZnO/RGO nanocomposites and their application to photocurrent generation. <i>Journal of Applied Physics</i> , 2014, 116, . | 2.5 | 132 |
| 2 | Synthesis and characterization of ZnO NPs/reduced graphene oxide nanocomposite prepared in gelatin medium as highly efficient photo-degradation of MB. <i>Ceramics International</i> , 2014, 40, 10217-10221. | 4.8 | 131 |
| 3 | One-pot sol-gel synthesis of reduced graphene oxide uniformly decorated zinc oxide nanoparticles in starch environment for highly efficient photodegradation of Methylene Blue. <i>RSC Advances</i> , 2015, 5, 21888-21896. | 3.6 | 116 |
| 4 | Enhancement of optical transmittance and electrical resistivity of post-annealed ITO thin films RF sputtered on Si. <i>Applied Surface Science</i> , 2018, 443, 544-547. | 6.1 | 80 |
| 5 | Crystalline quality assessment, photocurrent response and optical properties of reduced graphene oxide uniformly decorated zinc oxide nanoparticles based on the graphene oxide concentration. <i>RSC Advances</i> , 2015, 5, 53117-53128. | 3.6 | 40 |
| 6 | Structural, optical and electrical characterization of ITO, ITO/Ag and ITO/Ni transparent conductive electrodes. <i>Applied Surface Science</i> , 2014, 288, 599-603. | 6.1 | 33 |
| 7 | High Thermal Gradient in Thermo-electrochemical Cells by Insertion of a Poly(Vinylidene Fluoride) Membrane. <i>Scientific Reports</i> , 2016, 6, 29328. | 3.3 | 33 |
| 8 | Investigation of the electrochemical behavior of indium nitride thin films by plasma-assisted reactive evaporation. <i>RSC Advances</i> , 2015, 5, 17325-17335. | 3.6 | 27 |
| 9 | High performance InGaN LEDs on Si (111) substrates grown by MOCVD. <i>Journal Physics D: Applied Physics</i> , 2010, 43, 354008. | 2.8 | 25 |
| 10 | Effect of nitridation surface treatment on silicon (111) substrate for the growth of high quality single-crystalline GaN hetero-epitaxy layer by MOCVD. <i>Applied Surface Science</i> , 2016, 362, 572-576. | 6.1 | 25 |
| 11 | Plasma-assisted hot filament chemical vapor deposition of AlN thin films on ZnO buffer layer: toward highly c-axis-oriented, uniform, insulative films. <i>Applied Physics A: Materials Science and Processing</i> , 2014, 117, 2217-2224. | 2.3 | 24 |
| 12 | Indium Tin Oxide Coated D-Shape Fiber as a Saturable Absorber for Generating a Dark Pulse Mode-Locked Laser*. <i>Chinese Physics Letters</i> , 2020, 37, 054202. | 3.3 | 24 |
| 13 | Indium tin oxide coated D-shape fiber as saturable absorber for passively Q-switched erbium-doped fiber laser. <i>Optics and Laser Technology</i> , 2020, 124, 105998. | 4.6 | 23 |
| 14 | Effect of annealing on structural, optical, and electrical properties of nickel (Ni)/indium tin oxide (ITO) nanostructures prepared by RF magnetron sputtering. <i>Superlattices and Microstructures</i> , 2014, 70, 82-90. | 3.1 | 22 |
| 15 | Ammonia flux tailoring on the quality of AlN epilayers grown by pulsed atomic-layer epitaxy techniques on (0001)-oriented sapphire substrates via MOCVD. <i>CrystEngComm</i> , 2019, 21, 2009-2017. | 2.6 | 21 |
| 16 | Effect of low NH ₃ flux towards high quality semi-polar (11-22) GaN on m-plane sapphire via MOCVD. <i>Superlattices and Microstructures</i> , 2018, 117, 207-214. | 3.1 | 20 |
| 17 | Structural ordering, morphology and optical properties of amorphous Al _{1-x} In _x N thin films grown by plasma-assisted dual source reactive evaporation. <i>Journal of Alloys and Compounds</i> , 2015, 632, 741-747. | 5.5 | 17 |
| 18 | In-situ tuning of Sn doped In ₂ O ₃ (ITO) films properties by controlling deposition Argon/Oxygen flow. <i>Applied Surface Science</i> , 2019, 479, 1220-1225. | 6.1 | 17 |

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|----|--|-----|-----------|
| 19 | Poly(3-hexylthiophene-2,5-diyl) regioregular (P3HT) thin film as saturable absorber for passively Q-switched and mode-locked Erbium-doped fiber laser. <i>Optical Fiber Technology</i> , 2020, 54, 102073. | 2.7 | 17 |
| 20 | Correlation between indium content in monolithic InGaN/GaN multi quantum well structures on photoelectrochemical activity for water splitting. <i>Journal of Alloys and Compounds</i> , 2017, 706, 629-636. | 5.5 | 16 |
| 21 | The effect of sputtering pressure on structural, optical and electrical properties of indium tin oxide nanocolumns prepared by radio frequency (RF) magnetron sputtering. <i>Superlattices and Microstructures</i> , 2014, 72, 140-147. | 3.1 | 15 |
| 22 | Positioning of periodic AlN/GaN multilayers: Effect on crystalline quality of a-plane GaN. <i>Materials Science in Semiconductor Processing</i> , 2020, 105, 104700. | 4.0 | 15 |
| 23 | Mode-locked erbium-doped fiber laser via evanescent field interaction with indium tin oxide. <i>Optical Fiber Technology</i> , 2020, 55, 102124. | 2.7 | 15 |
| 24 | Embedded AlN/GaN multi-layer for enhanced crystal quality and surface morphology of semi-polar (11 $\bar{2}$ 2) GaN on m-plane sapphire. <i>Materials Science in Semiconductor Processing</i> , 2018, 86, 1-7. | 4.0 | 14 |
| 25 | Non-Polar Gallium Nitride for Photodetection Applications: A Systematic Review. <i>Coatings</i> , 2022, 12, 275. | 2.6 | 13 |
| 26 | Improved optoelectronics properties of ITO-based transparent conductive electrodes with the insertion of Ag/Ni under-layer. <i>Applied Surface Science</i> , 2014, 315, 387-391. | 6.1 | 12 |
| 27 | Observation of saturation transfer characteristics in solution processed vertical organic field-effect transistors (VOFETs) with high leakage current. <i>Current Applied Physics</i> , 2018, 18, 1415-1421. | 2.4 | 12 |
| 28 | Crystal quality and surface structure tuning of semi-polar (11 $\bar{2}$ 2) GaN on m-plane sapphire via in-situ multiple ammonia treatment. <i>Thin Solid Films</i> , 2020, 697, 137817. | 1.8 | 12 |
| 29 | Optimization of poly(vinylidene fluoride) membranes for enhanced power density of thermally driven electrochemical cells. <i>Journal of Materials Science</i> , 2017, 52, 10353-10363. | 3.7 | 11 |
| 30 | Standard pressure deposition of crack-free AlN buffer layer grown on c-plane sapphire by PALE technique via MOCVD. <i>Superlattices and Microstructures</i> , 2018, 120, 319-326. | 3.1 | 10 |
| 31 | The optimization of n-type and p-type m-plane GaN grown on m-plane sapphire substrate by metal organic chemical vapor deposition. <i>Materials Science in Semiconductor Processing</i> , 2021, 131, 105836. | 4.0 | 10 |
| 32 | Nanocolumnar zinc oxide as a transparent conductive oxide film for a blue InGaN-based light emitting diode. <i>Ceramics International</i> , 2015, 41, 913-920. | 4.8 | 9 |
| 33 | High figure of merit of the post-annealed Ti/Al/ITO transparent conductive contacts sputter deposited on n-GaN. <i>Journal of Alloys and Compounds</i> , 2016, 681, 186-190. | 5.5 | 9 |
| 34 | Impact of a Strained Periodic Multilayer on the Surface and Crystal Quality of a Semipolar (11 $\bar{2}$ 2) GaN Template. <i>Crystal Growth and Design</i> , 2019, 19, 6092-6099. | 3.0 | 9 |
| 35 | Growth of semi-polar $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.svg" \rangle \langle \text{mml:mrow} \langle \text{mml:mrow} \langle \text{mml:mo stretchy="true" \rangle \langle \text{mml:mn} 11 \rangle \langle \text{mml:mover} \rangle \text{Tj ETQq1 1 0.784314} \rangle \text{rgBT /Overlock 10}$ | 3.5 | 9 |
| 36 | In-Situ Multiple Ammonia Treatment (I-SMAT) method. <i>Vacuum</i> , 2020, 174, 109208. Impact of crystallinity towards the performance of semi-polar (11 $\bar{2}$ 2) GaN UV photodetector. <i>Materials Letters</i> , 2021, 286, 129244. | 2.6 | 9 |

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|----|---|-----|-----------|
| 37 | Effect of using two-step thermal annealing with different ambient gas on Mg activation and crystalline quality in GaN. Superlattices and Microstructures, 2015, 82, 592-598. | 3.1 | 8 |
| 38 | Effects of pulse cycle number on the quality of pulsed atomic-layer epitaxy AlN films grown via metal organic chemical vapor deposition. Japanese Journal of Applied Physics, 2019, 58, SC1037. | 1.5 | 8 |
| 39 | Agglomeration enhancement of AlN surface diffusion fluxes on a (0 0 0 1)-sapphire substrate grown by pulsed atomic-layer epitaxy techniques via MOCVD. CrystEngComm, 2020, 22, 3309-3321. | 2.6 | 7 |
| 40 | Growth of InGaN-based laser diode structure on silicon (111) substrate. Journal of Physics: Conference Series, 2009, 152, 012007. | 0.4 | 6 |
| 41 | Effect of Al _{0.06} Ga _{0.94} N/GaN Strained-Layer Superlattices Cladding Underlayer to InGaN-Based Multi-Quantum Well Grown on Si(111) Substrate with AlN/GaN Intermediate Layer. Japanese Journal of Applied Physics, 2010, 49, 021002. | 1.5 | 6 |
| 42 | Thermally Resistive Electrospun Composite Membranes for Low-Grade Thermal Energy Harvesting. Macromolecular Materials and Engineering, 2018, 303, 1700482. | 3.6 | 6 |
| 43 | Solution-Processable Vertical Organic Light-Emitting Transistors (VOLETs) with Directly Deposited Silver Nanowires Intermediate Source Electrode. Journal of Nanoscience and Nanotechnology, 2019, 19, 6995-7003. | 0.9 | 6 |
| 44 | PEDOT:PSS Thin Film as Transparent Electrode in ITO-Free Organic Solar Cell. Advanced Materials Research, 2012, 501, 252-256. | 0.3 | 5 |
| 45 | First-principles calculation of structural, optoelectronic properties of the cubic Al Ga In N quaternary alloys matching on AlN substrate, within modified Becke-Johnson (mBJ) exchange potential. Optik, 2016, 127, 11577-11587. | 2.9 | 5 |
| 46 | Metal organic chemical vapor deposition of m-plane GaN epi-layer using a three-step approach towards enhanced surface morphology. Thin Solid Films, 2018, 667, 48-54. | 1.8 | 5 |
| 47 | MEH-PPV organic material as saturable absorber for Q-switching and mode-locking applications. Journal of Modern Optics, 2020, 67, 746-753. | 1.3 | 5 |
| 48 | Improved performance of InGaN/GaN LED by optimizing the properties of the bulk and interface of ITO on p-GaN. Applied Surface Science, 2021, 540, 148406. | 6.1 | 5 |
| 49 | The effect of Multi Quantum Well growth regime transition on MQW/p-GaN structure and light emitting diode (LED) performance. Materials Science in Semiconductor Processing, 2021, 121, 105431. | 4.0 | 5 |
| 50 | Diminishing the Induced Strain and Oxygen Incorporation on Aluminium Nitride Films Deposited Using Pulsed Atomic-Layer Epitaxy Techniques at Standard Pressure MOCVD. Journal of Electronic Materials, 2021, 50, 2313-2322. | 2.2 | 5 |
| 51 | Compositional and Structural Characterization of Heterostructure InGaN-Based Light-Emitting Diode by High Resolution X-Ray Diffraction. Advanced Materials Research, 0, 620, 22-27. | 0.3 | 4 |
| 52 | InGaN-based multi-quantum well light-emitting diode structure with the insertion of superlattices under-layer. Superlattices and Microstructures, 2013, 60, 201-207. | 3.1 | 4 |
| 53 | Effect of indium pre-flow on wavelength shift and crystal structure of deep green light emitting diodes. Optical Materials Express, 2021, 11, 926. | 3.0 | 4 |
| 54 | Study of Annealed Nickel (Ni)/Indium Tin Oxide (ITO) Nanostructures Prepared by RF Magnetron Sputtering. Advanced Materials Research, 2013, 832, 695-699. | 0.3 | 3 |

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|----|---|-----|-----------|
| 55 | Effects of Pressure Dependence on Nanocolumnar Zinc Oxide Deposited by RF Magnetron Sputtering. <i>Advanced Materials Research</i> , 2013, 832, 787-791. | 0.3 | 3 |
| 56 | Nanostructured Al-doped ZnO-based gas sensor prepared using sol-gel spin-coating method. , 2014, , . | | 3 |
| 57 | Post-Annealing Effects on ITO Thin Films RF Sputtered at Different Thicknesses on Si and Glass. <i>Advanced Materials Research</i> , 0, 925, 411-415. | 0.3 | 3 |
| 58 | Effect of thermal interaction between bulk GaN substrates and corral sapphire on blue light emission InGaN/GaN multi-quantum wells by MOCVD. <i>Superlattices and Microstructures</i> , 2018, 119, 157-165. | 3.1 | 3 |
| 59 | Impact of sandwiched strain periodic multilayer AlN/GaN on strain and crystalline quality of a-plane GaN. <i>Scientific Reports</i> , 2021, 11, 9724. | 3.3 | 3 |
| 60 | Magnesium doped semipolar (11 $\bar{1}$ 2) p-type gallium nitride: Impact of dopant concentration variants towards grain size distributions and crystalline quality. <i>Thin Solid Films</i> , 2022, 741, 139003. | 1.8 | 3 |
| 61 | Structural and Optical Properties of Nickel-Doped Zinc Oxide Thin Film on Nickel Seed Layer Deposited by RF Magnetron Sputtering Technique. <i>Advanced Materials Research</i> , 0, 895, 3-7. | 0.3 | 2 |
| 62 | Development of atmospheric pressure plasma needle jet for sterilization applications. <i>AIP Conference Proceedings</i> , 2017, , . | 0.4 | 2 |
| 63 | The crystallographic quality and band-edge transition of as-deposited PALE AlN films via metal organic chemical vapor deposition. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 3211-3221. | 2.2 | 2 |
| 64 | Enhanced indium adsorption and surface evolution of semi-polar (11 $\bar{1}$ 2) LED via a strain periodic alternating superlattice (SPAS-L). <i>Materials Today Communications</i> , 2021, 27, 102441. | 1.9 | 2 |
| 65 | Effect of Flux Rate Variation at Fixed V/III Ratio on Semi-Polar (112 $\bar{2}$) GaN: Crystal Quality and Surface Morphology Study. <i>Crystals</i> , 2022, 12, 247. | 2.2 | 2 |
| 66 | Effect of AlGaIn $\bar{1}$ GaN Strained-Layer Superlattices Underlayer to InGaIn-based Multi-Quantum Wells Grown on Si(111) Substrate by MOCVD. , 2011, , . | | 1 |
| 67 | Electrical and Optical Characterization of Mg Doping in GaN. <i>Advanced Materials Research</i> , 0, 620, 453-457. | 0.3 | 1 |
| 68 | Effect of Substrate Temperature on Structural and Morphological Properties of Indium Tin Oxide Nanocolumns Using RF Magnetron Sputtering. <i>Advanced Materials Research</i> , 2014, 895, 12-16. | 0.3 | 1 |
| 69 | Structural and Optical Properties of Nickel (Ni)/indium Tin Oxide (ITO) Thin-Films Deposited by RF Magnetron Sputtering. <i>Advanced Materials Research</i> , 2014, 895, 181-185. | 0.3 | 1 |
| 70 | Characterization of ITO/Ag and ITO/Ni Bi-Layer Transparent Conductive Electrodes. <i>Advanced Materials Research</i> , 0, 1024, 75-78. | 0.3 | 1 |
| 71 | Fabrications of Nanocomposite Gold-Polymer Metamaterials Consisting of Periodic Microcavities with Tunable Optical Properties. <i>Optik</i> , 2017, 150, 54-61. | 2.9 | 1 |
| 72 | Effect of working power and pressure on plasma properties during the deposition of TiN films in reactive magnetron sputtering plasma measured using Langmuir probe measurement. <i>Journal of Physics: Conference Series</i> , 2018, 995, 012068. | 0.4 | 1 |

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|----|--|-----|-----------|
| 73 | Fabrication of In _x Ga _{1-x} N/GaN Multi-Quantum well Structure for Green Light Emitting Diode on Patterned Sapphire Substrate by Metal Organic Chemical Vapour Deposition. Solid State Phenomena, 2019, 290, 147-152. | 0.3 | 1 |
| 74 | Improving Material Quality of Polycrystalline GaN by Manipulating the Etching Time of a Porous AlN Template. Journal of Electronic Materials, 2019, 48, 3547-3553. | 2.2 | 1 |
| 75 | Alq ₃ saturable absorber for generating Q-switched pulses in erbium-doped fiber laser. Microwave and Optical Technology Letters, 2020, 62, 1028-1032. | 1.4 | 1 |
| 76 | Influence of post-ammonia annealing temperature on e-beam evaporation deposited GaN layer on patterned sapphire substrate. Superlattices and Microstructures, 2020, 148, 106722. | 3.1 | 1 |
| 77 | Disilane doping of semi-polar (11-22) n-GaN: The impact of terrace-like evolution toward the enhancement of the electrical properties. Thin Solid Films, 2021, 720, 138489. | 1.8 | 1 |
| 78 | Effect of nucleation layer thickness on reducing dislocation density in AlN layer for AlGaIn-based UVC LED. Microelectronics International, 2021, 38, 113-118. | 0.6 | 1 |
| 79 | Improvement of c-axis (002) AlN crystal plane by temperature assisted HiPIMS technique. Microelectronics International, 2021, 38, 86-92. | 0.6 | 1 |
| 80 | Luminescence and Crystalline Properties of InGaIn-based LED on Si Substrate with AlN/GaN Superlattice Structure. Journal of Physical Science, 2021, 32, 1-11. | 0.9 | 1 |
| 81 | InGaIn-based blue LED grown on Si(111) substrate. , 2011, , . | | 0 |
| 82 | Structural properties of InGaIn-based light-emitting diode epitaxial growth on Si (111) with AlN/InGaIn buffer layer. , 2012, , . | | 0 |
| 83 | Electronic properties and electrical characteristics of modified PEDOT:PSS as a buffer layer in organic solar cell. , 2012, , . | | 0 |
| 84 | Influence of Substrate Temperature on Morphological and Electrical Properties of Indium Tin Oxide Nanocolumns Prepared by RF Magnetron Sputtering. Advanced Materials Research, 2013, 832, 281-285. | 0.3 | 0 |
| 85 | Effects of Oxygen Gas Composition on Nanocolumnar Zinc Oxide Properties Deposited by RF Magnetron Sputtering. Advanced Materials Research, 0, 832, 783-786. | 0.3 | 0 |
| 86 | A Study on the Seebeck Effect of 3,4,9,10-Perylenetetracarboxylic Dianhydride (PTCDA) as a Novel N-Type Material in a Thermoelectric Device. Advanced Materials Research, 2013, 667, 165-171. | 0.3 | 0 |
| 87 | Influence of RF Magnetron Sputtering Pressure on the Structural, Optical, and Morphological Properties of Indium Tin Oxide Nanocolumns. Advanced Materials Research, 2013, 832, 276-280. | 0.3 | 0 |
| 88 | Effect of Annealing on Surface of Nickel (Ni)/Indium Tin Oxide (ITO) Nanostructures Measured by Atomic Force Microscopy (AFM). Advanced Materials Research, 2013, 832, 51-55. | 0.3 | 0 |
| 89 | Numerical estimation of self-sputtering effect in ionized physical vapor deposition system. , 2014, , . | | 0 |
| 90 | Effects of Growth Temperature on the Structural Properties of Zinc Oxide Nanograins Deposited by RF Magnetron Sputtering. Advanced Materials Research, 2014, 895, 500-504. | 0.3 | 0 |

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|-----|--|-----|-----------|
| 91 | Effect of Sn dopant concentration on structural and electrical properties of ZnO nanostructures based methane gas sensor. , 2015, , . | | 0 |
| 92 | Modeling and simulation of metal organic halide vapor phase epitaxy (MOHVPE) growth chamber. Microsystem Technologies, 2015, 21, 309-318. | 2.0 | 0 |
| 93 | Fabrication of nanostructured Al-doped ZnO thin film for methane sensing applications. AIP Conference Proceedings, 2016, , . | 0.4 | 0 |
| 94 | Nitrogen emission in reactive magnetron sputtering plasmas during the deposition of titanium nitride thin film. AIP Conference Proceedings, 2017, , . | 0.4 | 0 |
| 95 | Synthesis and characterization of InN nanocrystals on glass substrate by plasma assisted reactive evaporation. AIP Conference Proceedings, 2017, , . | 0.4 | 0 |
| 96 | Surface and optical characteristics of polycrystalline GaN layer with different pores profile of porous GaAs/GaAs substrate. Materials Research Express, 2019, 6, 085906. | 1.6 | 0 |
| 97 | Effect of the Bias Voltage on the Polycrystalline a-axis Oriented AlN Thin Films by RF Sputtering. , 2019, , . | | 0 |
| 98 | Electronic surface, optical and electrical properties of p μ GaN activated via in-situ MOCVD and ex-situ thermal annealing in InGaN/GaN LED. Materials Science in Semiconductor Processing, 2020, 106, 104757. | 4.0 | 0 |
| 99 | Structural and mechanical properties of a-axis AlN thin films growth using reactive RF magnetron sputtering plasma. Microelectronics International, 2021, 38, 99-104. | 0.6 | 0 |
| 100 | Anodization voltage effect on physical properties of anodic TiO ₂ nanotube arrays film. AIP Conference Proceedings, 2020, , . | 0.4 | 0 |